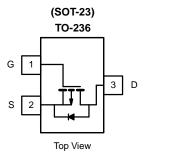
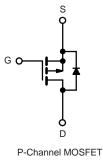


RAQ045P01TCR-VB Datasheet

P-Channel 30 V (D-S) MOSFET

PRODUC	CT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω) Typ.	I _D (A) ^a	Q _g (Typ.)
	0.046 at V _{GS} = - 10 V	- 5.6	
- 30	0.049 at V _{GS} = - 6 V	- 5	11.4 nC
	0.054 at V _{GS} = - 4.5 V	-4.5	





FEATURES

- Trench Power MOSFET
- 100 % R_g Tested



- For Mobile Computing
 - Load Switch
 - Notebook Adaptor Switch
 - DC/DC Converter

Pb-free
RoHS
COMPLIANT
HALOGEN
EDEE

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	- 30	N
Gate-Source Voltage		V _{GS}	± 20	V
	T _C = 25 °C		- 5.6	
Continuous Drain Current (T. 150 °C)	T _C = 70 °C		- 5.1	
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _A = 25 °C	I _D	- 5.4 ^{b,c}	
	T _A = 70 °C		- 4.3 ^{b,c}	A
Pulsed Drain Current (t = 100 µs)		I _{DM}	- 18	
Continuus Source Drain Diado Current	T _C = 25 °C		- 2.1	
ontinous Source-Drain Diode Current	T _A = 25 °C	I _S	- 1 ^{b,c}	
	T _C = 25 °C		2.5	
Marian David Distinction	T _C = 70 °C		1.6	14/
Maximum Power Dissipation	T _A = 25 °C	P _D	1.25 ^{b,c}	W
	T _A = 70 °C	1	0.8 ^{b,c}	
Operating Junction and Storage Temperatur	e Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b,d}	$t \le 5 s$	R _{thJA}	75	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	0/10

Notes:

a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 166 °C/W.

$\begin{split} \textbf{SPECIFICATIONS}(T_{j} = 25 °C, unless otherwise noted) \\ \hline Parameter Source Breakdown Voltage VDB Source Treshold Voltage VDB VDB VDB VDB - 250 \muA - 30 MD VDB VDB - 250 \muA - 30 MD VDB VDB VDB - 250 \muA - 30 MD VDB VDB - 19 MD VDB - 19 MD VDB - 19 MD VDB - 250 \muA - 4 MD VDB - 19 MD VDB - 250 \muA - 19 MD VDB - 19 MD A - 10 MD VDB - 250 \muA - 10 - 19 MD VDB - 250 \muA - 0.5 MD - 10 MD VDB - 250 \muA - 0.5 MD - 2.0 MD A - 2.0 VDB - 250 \muA - 0.5 MD - 2.0 MD A - 2.0 VDB - 250 \muA - 0.5 MD - 2.0 MD A - 2.0 VDB - 250 \muA - 0.5 MD - 2.0 MD - 2.5 MD - 2.5$							
	SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$,	unless othe	erwise noted)				
$\begin{array}{ c c c c c c } \hline Drain-Source Breakdown Voltage & V_DS & V_GS = 0 V, I_D = -250 \ \mu A & -30 & & V \\ V_DS temperature Coefficient & \Delta V_{OS}^{TJ} & I_D = -250 \ \mu A & -19 & & \\ & I_D = -250 \ \mu A & -0.5 & -2.0 & V \\ \hline Gate-Source Threshold Voltage & V_{OS}(m) & V_{DS} = V_{OS}, I_D = -250 \ \mu A & -0.5 & -2.0 & V \\ \hline Gate-Source Threshold Voltage & V_{OS}(m) & V_{DS} = 0 V, V_{GS} = 20 \ V & = 10 & nA \\ \hline V_{DS} = -30 \ V_{OS} = 0 \ V, V_{OS} = 0 \ V & = 55 \ C & -5 & A \\ \hline V_{DS} = -30 \ V_{OS} = 0 \ V, V_{OS} = 0 \ V & -2.5 & A \\ \hline On-State Drain Current^{0} & I_D(m) & V_{DS} = -54 \ A & 0.046 & & \\ \hline V_{OS} = -6V, V_{OS} = -10 \ V, I_D = -3.4 \ A & 0.046 & & \\ \hline V_{OS} = -6V, V_{OS} = -10 \ V, I_D = -3.4 \ A & 0.046 & & \\ \hline Oracle A \ V_{OS} = -15 \ V, V_{OS} = 0 \ V, I_D = -3.4 \ A & 18 & & \\ \hline Drain-Source On-State Resistance^{0} & Q_{B} & V_{DS} = -15 \ V, V_{OS} = -10 \ V, I_D = -5.4 \ A & 18 & & \\ \hline Drain-Capacitance & C_{ms} & & \\ \hline Drain-Gatiance & C_{ms} & & \\ \hline Total Gate Charge & Q_{g} & V_{DS} = -15 \ V, V_{OS} = -10 \ V, I_D = -5.4 \ A & 3.4 & & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & V_{DS} = -15 \ V, V_{OS} = -10 \ V, I_D = -5.4 \ A & 3.4 & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & \\ \hline Drain-Source Dorbin Charace & R_{g} & f = 1 \ MHz & 1.5 \ 7.7 \ 15.4 \ Q \ C & \\ \hline Drain-Source Drain Dide Characetristics & \\ \hline Turn-On Delay Time & I_4 \ U_{d(m)} & \\ \hline Drain-Source Drain Dide Characetristics & \\ \hline Drain-Source Drain Di$	Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Static				1	1	1
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$	- 30			V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	la = - 250 µA		- 19		m\//°C
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	10 - 200 p/		4		IIIV/ C
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 0.5		- 2.0	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Zerra Octo Malta va Davia Octoval	1	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	
$ \begin{array}{ c c c c c c } \hline V_{GS} & -10 \ V, \ I_D = \cdot 4.4 \ A & 0.046 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.046 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.046 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline V_{GS} & -6 \ V, \ I_D = \cdot 4.4 \ A & 0.049 & \\ \hline U_{DS} & -15 \ V, \ V_{GS} = -15 \ V, \ V$	Zero Gate voltage Drain Current	DSS	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 5	μΑ
$ \begin{array}{ c c c c c c } \hline Drain-Source On-State Resistance^a & R_{DS(on)} & V_{GS} = -6 \ V, \ I_D = -4 \ A & 0.049 & I & 0.049 & I & 0.049 & I & V_{GS} = -6 \ V, \ I_D = -3.6 \ A & 0.054 & I & S & I & S & I & I & S & S & I & I$	On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, V_{GS} = - 10 V	- 2.5			A
$ \begin{array}{ c c c c c c c c } \hline V_{GS} = -4.5 \ V, \ I_{D} = -3.6 \ A & 0.054 \\ \hline V_{CS} = -4.5 \ V, \ I_{D} = -3.4 \ A & 18 \\ \hline V_{DS} = -15 \ V, \ V_{DS} = -15 \ V, \ I_{D} = -3.4 \ A & 18 \\ \hline S \\ \hline \hline Dynamicb \\ \hline \\ $			V _{GS} =- 10 V, I _D = - 4.4 A		0.046		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} =- 6 V, I _D = - 4 A		0.049		Ω
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			V _{GS} =- 4.5 V, I _D = - 3.6 A		0.054		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3.4 A		18		S
$ \begin{array}{ c c c c c } \hline \mbox{Output Capacitance} & \mbox{C}_{0ss} & \mbox{V}_{DS} = -15 \ V, \ V_{GS} = 0 \ V, \ f = 1 \ MHz & 150 & \mbox{M} & \m$	Dynamic ^b	•	•				•
$ \begin{array}{ c c c c c } \hline \mbox{Output Capacitance} & \mbox{C}_{0ss} & \mbox{V}_{DS} = -15 \ V, \ V_{GS} = 0 \ V, \ f = 1 \ MHz & 150 & \mbox{M} & \m$	Input Capacitance	C _{iss}			1295		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Output Capacitance		V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		150		рF
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Reverse Transfer Capacitance	C _{rss}			130		
$ \begin{array}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	Tatal Qata Ohanna		V_{DS} = - 15 V, V_{GS} = - 10 V, I_{D} = - 5.4 A		24	36	
$ \begin{array}{ c c c c c c } \hline Gate-Source Charge & Q_{gs} & V_{DS} = -15 \ V, \ V_{GS} = -4.5 \ V, \ I_D = -5.4 \ A & 3.4 & & & & & & \\ \hline Gate-Drain Charge & Q_{gd} & & & & & & & & & \\ \hline Gate Resistance & R_g & f = 1 \ MHz & 1.5 & 7.7 & 15.4 & \Omega & & \\ \hline Iurn-On \ Delay Time & t_{d(on)} & & & & & & & & \\ \hline Turn-On \ Delay Time & t_r & & & & & & & & & & \\ \hline Iurn-Off \ Delay Time & t_f & & & & & & & & & & & & \\ \hline Iurn-Off \ Delay Time & t_f & & & & & & & & & & & & & & & \\ \hline Iurn-On \ Delay Time & t_f & & & & & & & & & & & & & & & & & \\ \hline Iurn-On \ Delay Time & t_f & & & & & & & & & & & & & & & & & & \\ \hline Iurn-On \ Delay Time & t_f & & & & & & & & & & & & & & & & & & &$	Iotal Gate Charge	Qg			11.4	17	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_{D} = - 5.4 A		3.4		nC
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate-Drain Charge				3.8		
$ \begin{array}{ c c c c c } \hline Rise Time & t_r & V_{DD} = -15 \ V, \ R_L = 3.5 \ \Omega & 1 & 4 & 8 \\ \hline Turn-Off \ Delay Time & t_{d(off)} & I_D = -4.3 \ A, \ V_{GEN} = -10 \ V, \ R_g = 1 \ \Omega & 38 & 57 \\ \hline Fall Time & t_f & 6 & 12 \\ \hline Turn-On \ Delay Time & t_{d(on)} & V_{DD} = -15 \ V, \ R_L = 3.5 \ \Omega & 16 & 24 \\ \hline Rise Time & t_r & V_{DD} = -15 \ V, \ R_L = 3.5 \ \Omega & 16 & 24 \\ \hline Turn-Off \ Delay Time & t_{d(off)} & I_D = -4.3 \ A, \ V_{GEN} = -4.5 \ V, \ R_g = 1 \ \Omega & 30 & 45 \\ \hline Fall Time & t_f & 10 & 20 \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Gate Resistance	R _g	f = 1 MHz	1.5	7.7	15.4	Ω
$ \begin{array}{ c c c c c } \hline Rise Time & t_r & V_{DD} = -15 \ V, \ R_L = 3.5 \ \Omega & 1 & 4 & 8 \\ \hline Turn-Off \ Delay Time & t_{d(off)} & I_D = -4.3 \ A, \ V_{GEN} = -10 \ V, \ R_g = 1 \ \Omega & 38 & 57 \\ \hline Fall Time & t_f & 6 & 12 \\ \hline Turn-On \ Delay Time & t_{d(on)} & V_{DD} = -15 \ V, \ R_L = 3.5 \ \Omega & 16 & 24 \\ \hline Rise Time & t_r & V_{DD} = -15 \ V, \ R_L = 3.5 \ \Omega & 16 & 24 \\ \hline Turn-Off \ Delay Time & t_{d(off)} & I_D = -4.3 \ A, \ V_{GEN} = -4.5 \ V, \ R_g = 1 \ \Omega & 30 & 45 \\ \hline Fall Time & t_f & 10 & 20 \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Turn-On Delay Time	t _{d(on)}			13	20	
$\begin{tabular}{ c c c c c c } \hline Fail Time & t_f & & & & & & & & & & & & & & & & & & &$	Rise Time		V_{DD} = - 15 V, R_L = 3.5 Ω		4	8	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 4.3 A, V_GEN = - 10 V, R_g = 1 Ω		38	57	
$\begin{tabular}{ c c c c c c c } \hline Turn-On Delay Time & t_d(on) & & & & & & & & & & & & & & & & & & &$	Fall Time	t _f			6	12	
$\begin{tabular}{ c c c c c c c c c c c } \hline Turn-Off Delay Time & t_{d(off)} & I_D\cong-4.3 \ A, \ V_{GEN}=-4.5 \ V, \ R_g=1 \ \Omega & 30 & 45 \\ \hline fall Time & t_f & 10 & 20 \\ \hline \end{tabular}$	Turn-On Delay Time	t _{d(on)}			28	42	ns
Fall Time t_f 1020Drain-Source Body Diode CharacteristicsContinuous Source-Drain Diode Current I_S $T_C = 25 ^{\circ}C$ -2.1 A Pulse Diode Forward Current (t = 100 µs) I_{SM} $I_S = -4.3 A, V_{GS} = 0 V$ -0.8 -1.2 V Body Diode Voltage V_{SD} $I_S = -4.3 A, V_{GS} = 0 V$ -0.8 -1.2 V Body Diode Reverse Recovery Time t_{rr} $I_F = -4.3 A, dI/dt = 100 A/\mus, T_J = 25 ^{\circ}C$ 7 14 nC Reverse Recovery Fall Time t_a T_a R_a R_a R_a R_a	Rise Time	t _r	V_{DD} = - 15 V, R_L = 3.5 Ω		16	24	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 4.3 A, V_GEN = - 4.5 V, R_g = 1 Ω		30	45	
$\begin{array}{c c c c c c c c c } \hline Continuous Source-Drain Diode Current & I_S & T_C = 25 \ ^{\circ}C & & -2.1 & \\ \hline Pulse Diode Forward Current (t = 100 \ \mu s) & I_{SM} & & -80 & \\ \hline Body Diode Voltage & V_{SD} & I_S = -4.3 \ A, \ V_{GS} = 0 \ V & -0.8 & -1.2 & V & \\ \hline Body Diode Reverse Recovery Time & t_{rr} & & 15 & 23 & ns & \\ \hline Body Diode Reverse Recovery Charge & Q_{rr} & & \\ \hline Reverse Recovery Fall Time & t_a & & & \\ \hline \end{array}$	Fall Time				10	20	
Pulse Diode Forward Current (t = 100 μ s)I_SM- 80ABody Diode VoltageV_SDI_S = - 4.3 A, V_{GS} = 0 V- 0.8- 1.2VBody Diode Reverse Recovery Time t_{rr} 1523nsBody Diode Reverse Recovery Charge Q_{rr} $I_F = -4.3 A, dl/dt = 100 A/\mus, T_J = 25 °C$ 714nCReverse Recovery Fall Time t_a nsnsns	Drain-Source Body Diode Characteristic	cs			1	1	1
Pulse Diode Forward Current (t = 100 µs) I_{SM} - 80Body Diode Voltage V_{SD} $I_S = -4.3 \text{ A}, V_{GS} = 0 \text{ V}$ - 0.8- 1.2VBody Diode Reverse Recovery Time t_{rr} 1523nsBody Diode Reverse Recovery Charge Q_{rr} $I_F = -4.3 \text{ A}, dI/dt = 100 \text{ A/µs}, T_J = 25 \text{ °C}$ 714nCReverse Recovery Fall Time t_a nsnsns	Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 2.1	٨
Body Diode Reverse Recovery Time t_{rr} 1523nsBody Diode Reverse Recovery Charge Q_{rr} Reverse Recovery Fall Time t_a	Pulse Diode Forward Current (t = 100 µs)	I _{SM}				- 80	
Body Diode Reverse Recovery Charge Q_{rr} $I_F = -4.3 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$ 714nCReverse Recovery Fall Time t_a 8ns	Body Diode Voltage	V _{SD}	$I_{S} = -4.3 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.8	- 1.2	V
Body Diode Reverse Recovery Charge Q_{rr} $I_F = -4.3 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$ 714nCReverse Recovery Fall Time t_a 8ns	Body Diode Reverse Recovery Time	t _{rr}			15	23	ns
Reverse Recovery Fall Time t _a	Body Diode Reverse Recovery Charge	Q _{rr}			7	14	nC
ns ns	Reverse Recovery Fall Time	ta	$I_F = -4.3 \text{ A}, \text{ ul/ul} = 100 \text{ A/} \mu \text{s}, I_J = 25 \text{ °C}$		8		
	Reverse Recovery Rise Time		1 1		7		ns

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

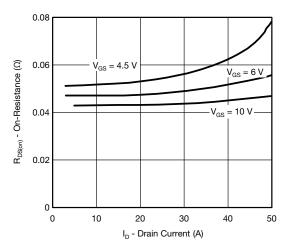




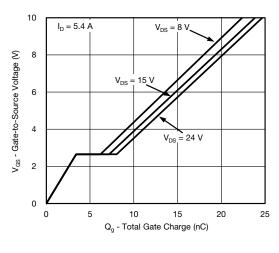




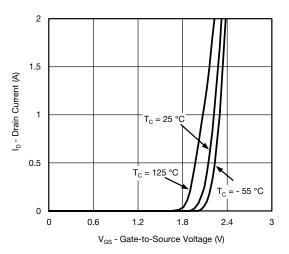
Output Characteristics



On-Resistance vs. Drain Current



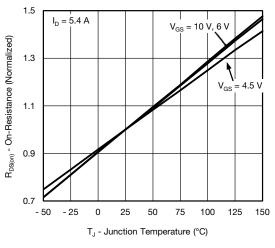
Gate Charge



Transfer Characteristics



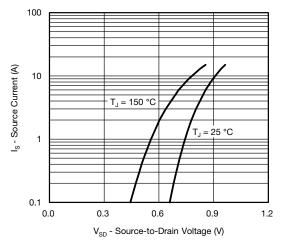
Capacitance



On-Resistance vs. Junction Temperature



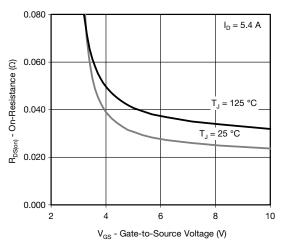
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



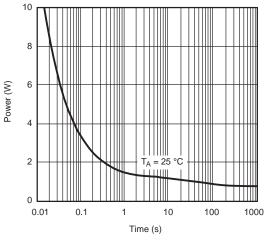
Source-Drain Diode Forward Voltage



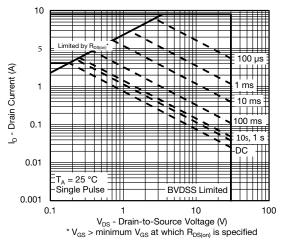
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



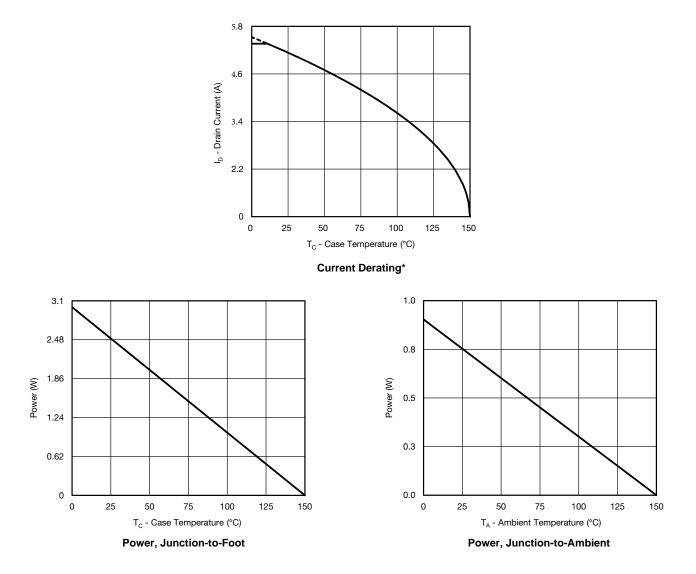
Single Pulse Power (Junction-to-Ambient)



Safe Operating Area, Junction-to-Ambient



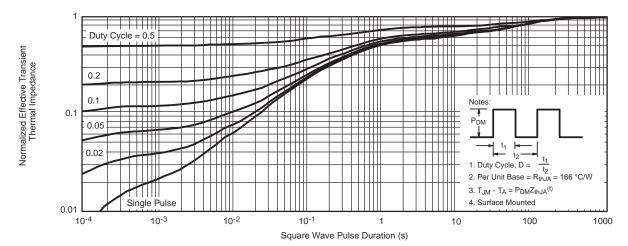
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



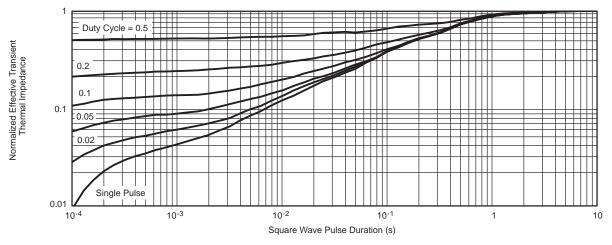
* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



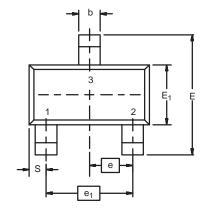
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Max 1.12 0.10 1.02 0.50 0.18 3.04 2.64 1.40	Min 0.035 0.0004 0.0346 0.014 0.003 0.110 0.083	Max 0.044 0.004 0.040 0.020 0.007 0.120 0.104		
0.10 1.02 0.50 0.18 3.04 2.64	0.0004 0.0346 0.014 0.003 0.110 0.083	0.004 0.040 0.020 0.007 0.120		
1.02 0.50 0.18 3.04 2.64	0.0346 0.014 0.003 0.110 0.083	0.040 0.020 0.007 0.120		
0.50 0.18 3.04 2.64	0.014 0.003 0.110 0.083	0.020 0.007 0.120		
0.18 3.04 2.64	0.003 0.110 0.083	0.007 0.120		
3.04 2.64	0.110 0.083	0.120		
2.64	0.083			
		0.104		
1 40				
1.40	0.047	0.055		
0.95 BSC	0.037	4 Ref		
1.90 BSC		0.0748 Ref		
0.60	0.016	0.024		
0.64 Ref	0.025	5 Ref		
0.50 Ref	0.020) Ref		
8°	3°	8°		
_	0.64 Ref 0.50 Ref	0.64 Ref 0.025 0.50 Ref 0.020		

RAQ045P01TCR-VB



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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